ABSTRACT

A semiconductor device includes a substrate that includes a first region and a second region, a first active pattern on the first region and that extends in a first horizontal direction, a second active pattern on the second region and that extends in the first horizontal direction, a first etch stop layer on the first active pattern, a second etch stop layer on the second active pattern, a plurality of first nanosheets on the first etch stop layer and that are stacked in a vertical direction and include silicon germanium (SiGe), a plurality of second nanosheets on the second etch stop layer and that are stacked in the vertical direction, a first gate electrode on the first etch stop layer and that extends in a second horizontal direction, and a second gate electrode disposed on the second etch stop layer and that extends in the second horizontal direction.

FIG. 2